



GUVB-T11GD

TECHNICAL DATA



UV-B Sensor

Features

- Aluminium Gallium Nitride Based Material
- Schottky-type Photodiode
- Photovoltaic Mode Operation
- High Responsivity & Low Dark Current

Applications

- UV-B Lamp Monitoring
- UV Index Monitoring

Absolute Maximum Ratings

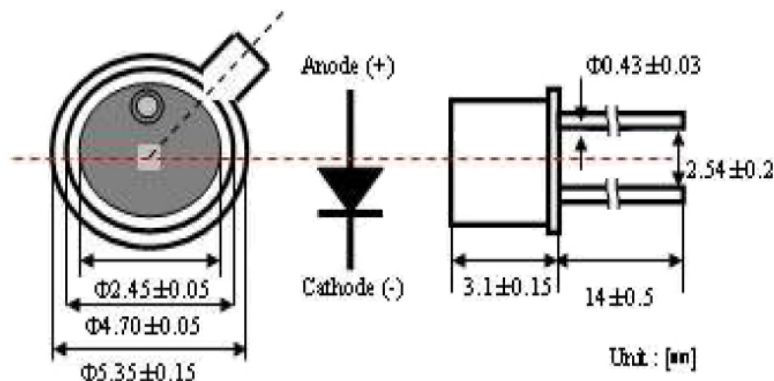
Item	Symbol	Value	Unit
Forward Current	I_F	1	mA
Reverse Voltage	V_R	3	V
Operating Temperature	T_{op}	-30 ... +85	°C
Storage Temperature	T_{st}	-40 ... +90	°C
Soldering Temperature *	T_{sol}	260	°C

* must be completed within 10 seconds

Characteristics (25°C)

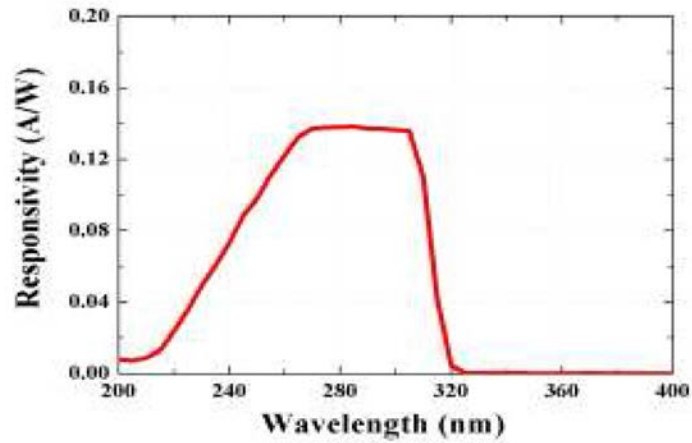
Item	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Dark Current	I_D	$V_R = 0.1 V$			1	nA
Photo Current	I_{PD}	UVB Lamp, 1 mW/cm ²		77		nA
		1 UVI		1.7		nA
Temperature Coefficient	I_{TC}	UVB Lamp		0.1		% / °C
Responsivity	R	$\lambda = 300 nm, V_R = 0 V$		0.13		A/W
Spectral Detection Range	λ	10% of R	220		320	nm

Package Dimension





Responsivity Curve



Photocurrent along UV Power

